

**UHF power transistor**

**BLW80**

**Description:**

N-P-N silicon planar epitaxial transistor intended for transmitting applications in class-A, B or C in the UHF and VHF range for nominal supply voltages up to 13.5 V. The resistance stabilization of the transistor provides protection against device damage at severe load mismatch conditions.

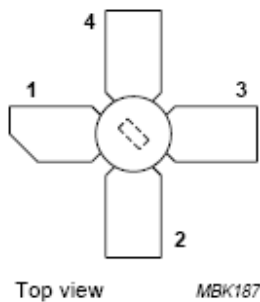
**Features:**

The transistor is housed in a 1/4" capstan envelope with a ceramic cap.

**Data:**

MODE OF OPERATION	V <sub>CE</sub> V	f MHz	P <sub>L</sub> W	G <sub>p</sub> dB	η %	$\bar{z}_i$ Ω	$\bar{Y}_L$ mS
c.w.	12,5	470	4	> 8,0	> 60	2,1 + j2,3	57 - j56
c.w.	12,5	175	4	typ. 15,0	typ. 60	2,0 - j2,2	51 - j48

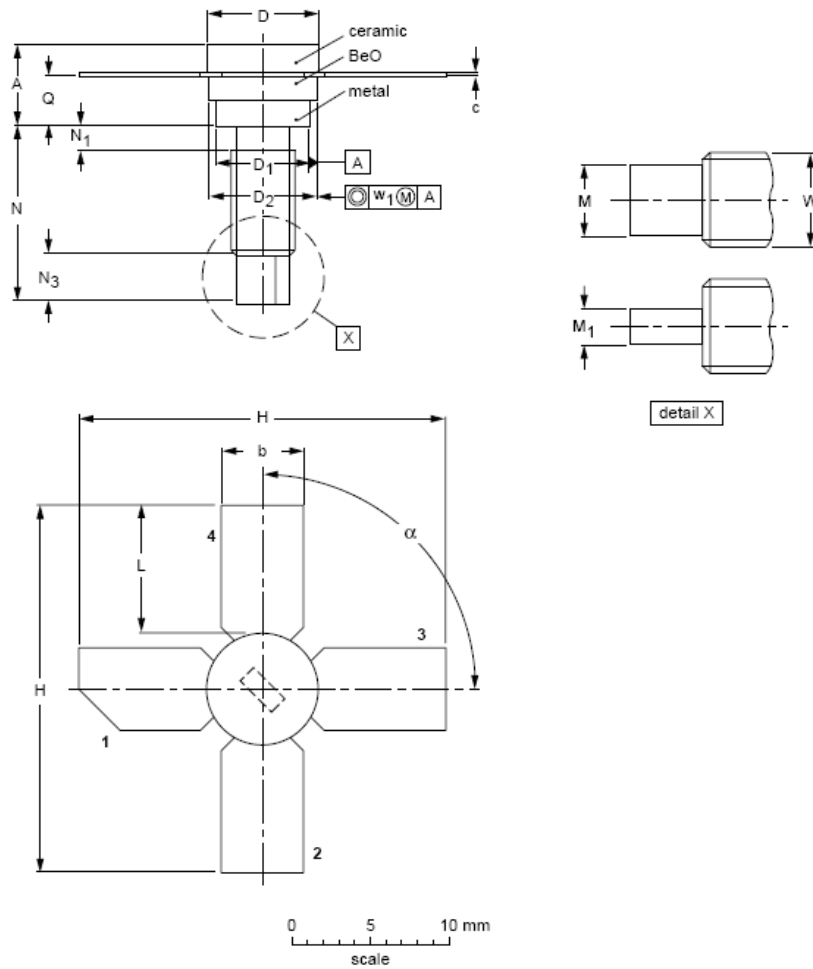
**Drawings:**



**PINNING - SOT122A.**

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter

Fig.1 Simplified outline. SOT122A.



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D <sub>1</sub>	D <sub>2</sub>	H	L	M <sub>1</sub>	M	N	N <sub>1</sub> max.	N <sub>3</sub>	Q	W	w <sub>1</sub>	α
mm	5.97 4.74	5.85 5.58	0.18 0.14	7.50 7.23	6.48 6.22	7.24 6.93	27.56 25.78	9.91 9.14	3.18 2.66	1.66 1.39	11.82 11.04	1.02	3.86 2.92	3.38 2.74	8-32 UNC	0.381	90°